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April 2001

FDC645N N-Channel PowerTrench[®] MOSFET

General Description

SEMICONDUCTOR IM

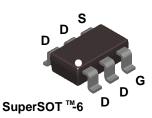
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$ and fast switching speed.

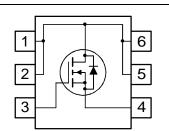
Applications

• DC/DC converter

Features

- 5.5 A, 30 V. $R_{DS(ON)} = 30 \text{ m}\Omega @ V_{GS} = 4.5 \text{ V}$ $R_{DS(ON)} = 26 \text{ m}\Omega @ V_{GS} = 10 \text{ V}$
- High performance trench technology for extremely low $R_{\text{DS}(\text{ON})}$
- Low gate charge (13 nC typical)
- High power and current handling capability





Absolute Maximum Ratings TA=25°C unless otherwise noted

| Symbol | | Parameter | Ratings | Units | | |
|-----------------------------------|---|----------------------------|----------------------------|------------|------------|--|
| V _{DSS} | Drain-Source Voltage | | | 30 | V | |
| V _{GSS} | Gate-Source Voltage | | | ±12 | V | |
| ID | Drain Curre | nt – Continuous | (Note 1a) | 5.5 | A | |
| | | Pulsed | | 20 | | |
| P _D | Maximum Power Dissipation (Note 1a) 1.6 | | 1.6 | W | | |
| | | | (Note 1b) | 0.8 | | |
| T _J , T _{STG} | Operating a | nd Storage Junction T | -55 to +150 | | | |
| Therma | I Charac | teristics | | | | |
| R _{0JA} | Thermal Resistance, Junction-to-Ambient (Note 1a) | | | 78 | °C/W | |
| R _{0JC} | Thermal Resistance, Junction-to-Case (Note 1) | | | 30 | °C/W | |
| | | g and Orderin | g Information Reel Size | Tape width | Quantity | |
| .645 | | FDC645N | 7" | | 3000 units | |

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FDC645N

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|---|--|--|-----|----------------|----------------|-------|
| Off Char | acteristics | | | | | |
| BV _{DSS} | Drain–Source Breakdown Voltage | $V_{GS} = 0 V, I_D = 250 \mu A$ | 30 | | | V |
| <u>ΔBV_{DSS}</u> ΔT _J | Breakdown Voltage Temperature Coefficient | I_D = 250 µA, Referenced to 25°C | | 22 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$ | | | 1 | μA |
| I _{GSSF} | Gate-Body Leakage, Forward | $V_{GS} = 12 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$ | | | 100 | nA |
| I _{GSSR} | Gate-Body Leakage, Reverse | $V_{GS} = -12 V, V_{DS} = 0 V$ | | | -100 | nA |
| On Char | acteristics (Note 2) | | | | | |
| V _{GS(th)} | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_{D} = 250 \ \mu A$ | 0.8 | 1.4 | 2 | V |
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate Threshold Voltage Temperature Coefficient | $I_D = 250 \ \mu\text{A}$, Referenced to 25°C | | - 4 | | mV/°C |
| R _{DS(on)} | Static Drain–Source On–Resistance | | | 25 23 34 | 30 26 48 | mΩ |
| I _{D(on)} | On-State Drain Current | $V_{GS} = 4.5 \text{ V}, V_{DS} = 5 \text{ V}$ | 20 | | | Α |
| g fs | Forward Transconductance | $V_{DS} = 10 V$, $I_D = 5.5 A$ | | 33 | | S |
| Dvnamio | Characteristics | | | | | |
| Ciss | Input Capacitance $V_{DS} = 15 \text{ V}, \text{ V}_{GS} = 0 \text{ V},$ | | | 1460 | | pF |
| Coss | Output Capacitance | f = 1.0 MHz | | 227 | | pF |
| Crss | Reverse Transfer Capacitance | | | 96 | | pF |
| Switchin | g Characteristics (Note 2) | | • | • | • | • |
| t _{d(on)} | Turn–On Delay Time | $V_{DS} = 15 V$, $I_D = 1 A$, | | 8 | 16 | ns |
| tr | Turn–On Rise Time | $V_{GS} = 4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$ | | 9 | 18 | ns |
| t _{d(off)} | Turn–Off Delay Time | | | 35 | 56 | ns |
| t _f | Turn–Off Fall Time | | | 7 | 14 | ns |
| Qg | Total Gate Charge | $V_{DS} = 15 V, I_D = 6.2 A,$ | | 13 | 21 | nC |
| Q _{gs} | Gate-Source Charge | $V_{GS} = 4.5 V$ | | 3.6 | | nC |
| Q _{gd} | Gate-Drain Charge | 7 | | 3.6 | | nC |
| Drain-S | ource Diode Characteristics | and Maximum Ratings | | | • | |
| ls | Maximum Continuous Drain–Source | | | | 1.3 | Α |
| V _{SD} | Drain–Source Diode Forward Voltage | $V_{GS} = 0 V$, $I_S = 1.3 A$ (Note 2) | | 0.7 | 1.2 | V |

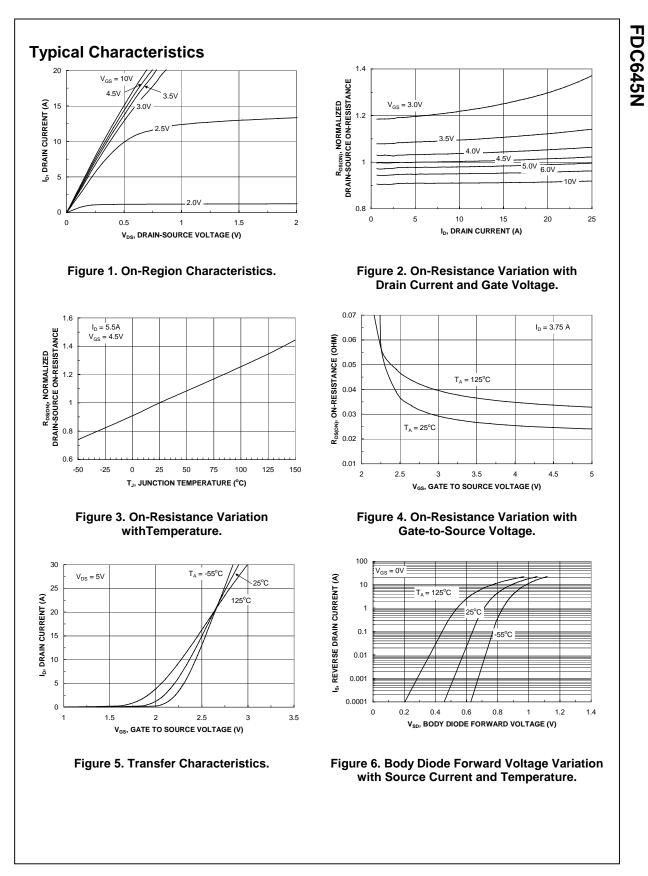
Notes:

1. R_{0JA} is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0CA} is determined by the user's board design.

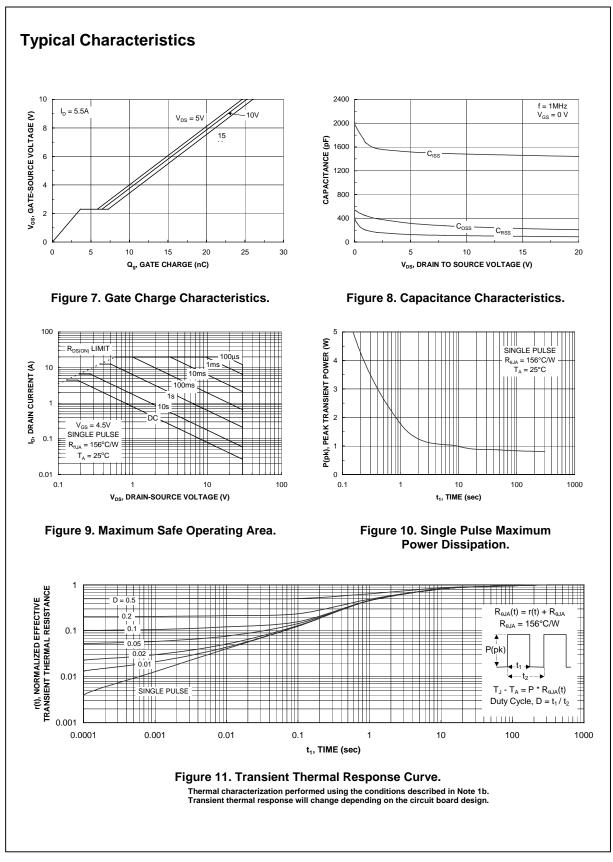
a. $~78^\circ\text{C/W}$ when mounted on a 1in^2 pad of 2oz copper on FR-4 board.

b. 156°C/W when mounted on a minimum pad.

2. Pulse Test: Pulse Width $\leq 300~\mu s,$ Duty Cycle $\leq 2.0\%$



FDC645N Rev C(W)



FDC645N

FDC645N Rev C(W)

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|--------------------------|---------------------------|---|--|--|
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